High Voltage Power Transistors

DPAK for Surface Mount Applications

Designed for line operated audio output amplifier, switchmode supply drivers and other switching applications.

Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Electrically Similar to Popular TIP47, and TIP50
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltage MJD47, NJVMJD47T4G MJD50, NJVMJD50T4G	V _{CEO}	250 400	Vdc
Collector–Base Voltage MJD47, NJVMJD47T4G MJD50, NJVMJD50T4G	V _{CB}	350 500	Vdc
Emitter-Base Voltage	V_{EB}	5	Vdc
Collector Current – Continuous	I _C	1	Adc
Collector Current – Peak	I _{CM}	2	Adc
Base Current	I _B	0.6	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	15 0.12	W W/°C
Total Power Dissipation (Note 1) @ T _A = 25°C Derate above 25°C	P _D	1.56 0.0125	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C
ESD – Human Body Model	HBM	3B	V
ESD – Machine Model	MM	С	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

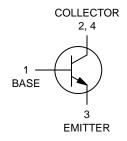
 These ratings are applicable when surface mounted on the minimum pad sizes recommended.



ON Semiconductor®

http://onsemi.com

NPN SILICON POWER TRANSISTORS 1 AMPERE 250, 400 VOLTS, 15 WATTS





DPAK CASE 369C STYLE 1

MARKING DIAGRAM



A = Assembly Location

Y = Year

WW = Work Week

Jxx = Device Code

xx = 47 or 50

G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction-to-Case	$R_{ heta JC}$	8.33	°C/W
Thermal Resistance Junction-to-Ambient (Note 2)	$R_{ heta JA}$	80	°C/W
Lead Temperature for Soldering Purpose	TL	260	°C

^{2.} These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	1		1	
Collector–Emitter Sustaining Voltage (Note 3) (I _C = 30 mAdc, I _B = 0) MJD47, NJVMJD47T4G MJD50, NJVMJD50T4G	V _{CEO(sus)}	250 400	- -	Vdc
Collector Cutoff Current $ \begin{array}{l} (\text{V}_{\text{CE}} = 150 \text{ Vdc, I}_{\text{B}} = 0) \\ \text{MJD47, NJVMJD47T4G} \\ (\text{V}_{\text{CE}} = 300 \text{ Vdc, I}_{\text{B}} = 0) \\ \text{MJD50, NJVMJD50T4G} \end{array} $	I _{CEO}	-	0.2 0.2	mAdc
Collector Cutoff Current	Ices		0.1 0.1	mAdc
Emitter Cutoff Current (V _{BE} = 5 Vdc, I _C = 0)	I _{EBO}	-	1	mAdc
ON CHARACTERISTICS (Note 3)				
DC Current Gain $(I_C = 0.3 \text{ Adc}, V_{CE} = 10 \text{ Vdc})$ $(I_C = 1 \text{ Adc}, V_{CE} = 10 \text{ Vdc})$	h _{FE}	30 10	150 -	_
Collector–Emitter Saturation Voltage (I _C = 1 Adc, I _B = 0.2 Adc)	V _{CE(sat)}	-	1	Vdc
Base–Emitter On Voltage (I _C = 1 Adc, V _{CE} = 10 Vdc)	V _{BE(on)}	-	1.5	Vdc
DYNAMIC CHARACTERISTICS	<u> </u>			
Current Gain – Bandwidth Product (I _C = 0.2 Adc, V _{CE} = 10 Vdc, f = 2 MHz)	f _T	10	-	MHz
Small–Signal Current Gain (I _C = 0.2 Adc, V _{CE} = 10 Vdc, f = 1 kHz)	h _{fe}	25	-	-
			•	

^{3.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

TYPICAL CHARACTERISTICS

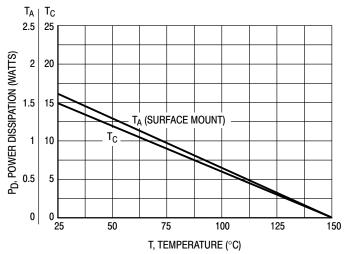


Figure 1. Power Derating

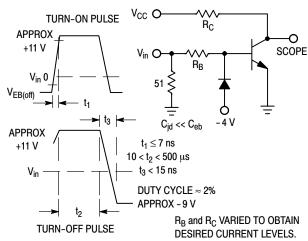


Figure 2. Switching Time Equivalent Circuit

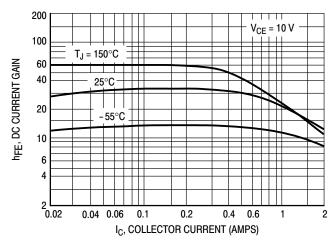


Figure 3. DC Current Gain

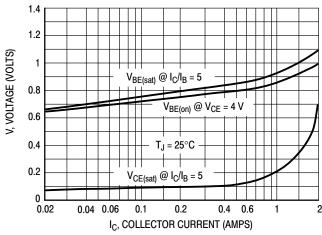


Figure 4. "On" Voltages

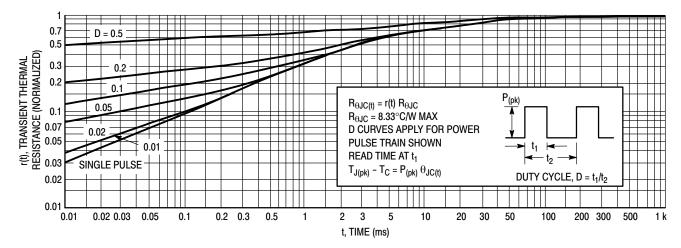


Figure 5. Thermal Response

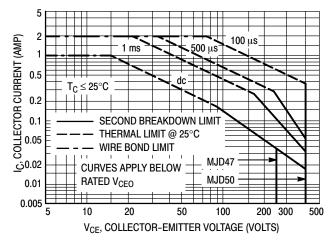


Figure 6. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on $T_{J(pk)} = 150^{\circ}\text{C}$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

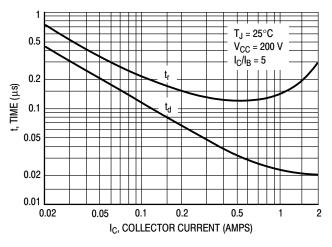


Figure 7. Turn-On Time

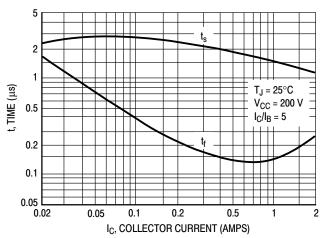


Figure 8. Turn-Off Time

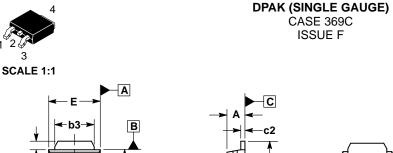
ORDERING INFORMATION

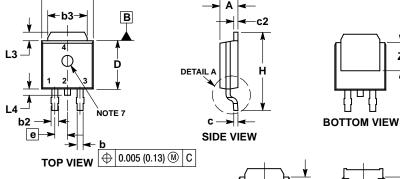
Device	Package	Shipping [†]
MJD47G	369C (Pb-Free)	75 Units / Rail
MJD47T4G	369C (Pb-Free)	2,500 / Tape & Reel
NJVMJD47T4G*	369C (Pb-Free)	2,500 / Tape & Reel
MJD50G	369C (Pb-Free)	75 Units / Rail
MJD50T4G	369C (Pb-Free)	2,500 / Tape & Reel
NJVMJD50T4G*	369C (Pb-Free)	2,500 / Tape & Reel

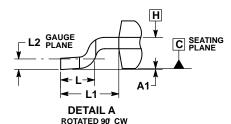
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging

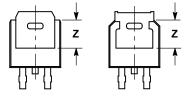
Specification Brochure, BRD8011/D.
*NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable.

DATE 21 JUL 2015





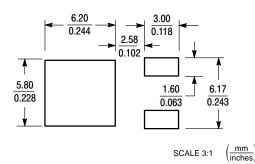




BOTTOM VIEW ALTERNATE CONSTRUCTIONS

STYLE 1: PIN 1. BASE 2. COLLE 3. EMITTI 4. COLLE	ER 3. SOL	AIN 2. CATI JRCE 3. ANO	HODE 2. ANODE DE 3. GATE	STYLE 5: PIN 1. GATE 2. ANODE 3. CATHODE 4. ANODE
STYLE 6:	STYLE 7:	3. ANODE	STYLE 9:	STYLE 10:
PIN 1. MT1	PIN 1. GATE		PIN 1. ANODE	PIN 1. CATHODE
2. MT2	2. COLLECTOR		2. CATHODE	2. ANODE
3. GATE	3. EMITTER		3. RESISTOR ADJUST	3. CATHODE
4. MT2	4. COLLECTOR		4. CATHODE	4. ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:

z

- IOTES. 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: INCHES. 3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-

- MENSIONS b3, L3 and Z.

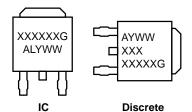
 Jimensions b And E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.

 MENSIONS D AND E ARE DETERMINED AT THE
- OUTERMOST EXTREMES OF THE PLASTIC BODY.

 6. DATUMS A AND B ARE DETERMINED AT DATUM
- 7. OPTIONAL MOLD FEATURE.

		INCHES		MILLIM	IETERS
	DIM	MIN	MAX	MIN	MAX
	Α	0.086	0.094	2.18	2.38
	A1	0.000	0.005	0.00	0.13
	b	0.025	0.035	0.63	0.89
ĺ	b2	0.028	0.045	0.72	1.14
	b3	0.180	0.215	4.57	5.46
	С	0.018	0.024	0.46	0.61
	c2	0.018	0.024	0.46	0.61
	D	0.235	0.245	5.97	6.22
	Е	0.250	0.265	6.35	6.73
	е	0.090	BSC	2.29	BSC
	Н	0.370	0.410	9.40	10.41
	L	0.055	0.070	1.40	1.78
	L1	0.114	REF	2.90	REF
ĺ	L2	0.020	BSC	0.51	BSC
	L3	0.035	0.050	0.89	1.27
	L4		0.040		1.01
	Z	0.155		3.93	

GENERIC MARKING DIAGRAM*



XXXXXX = Device Code = Assembly Location Α L = Wafer Lot Υ = Year

WW = Work Week G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking.

DOCUMENT NUMBER:	98AON10527D	E
STATUS:	ON SEMICONDUCTOR STANDARD	a ve
NEW STANDARD:	REF TO JEDEC TO-252	"(
DESCRIPTION:	DPAK SINGLE GAUGE SURFACE MOU	NT

Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.

PAGE 1 OF 2



DOCUMENT	NUMBER:
98AON10527	7D

PAGE 2 OF 2

ISSUE	REVISION	DATE
0	RELEASED FOR PRODUCTION. REQ. BY L. GAN	24 SEP 2001
Α	ADDED STYLE 8. REQ. BY S. ALLEN.	06 AUG 2008
В	ADDED STYLE 9. REQ. BY D. WARNER.	16 JAN 2009
С	ADDED STYLE 10. REQ. BY S. ALLEN.	09 JUN 2009
D	RELABELED DRAWING TO JEDEC STANDARDS. ADDED SIDE VIEW DETAIL A. CORRECTED MARKING INFORMATION. REQ. BY D. TRUHITTE.	29 JUN 2010
E	ADDED ALTERNATE CONSTRUCTION BOTTOM VIEW. MODIFIED DIMENSIONS b2 AND L1. CORRECTED MARKING DIAGRAM FOR DISCRETE. REQ. BY I. CAMBALIZA.	06 FEB 2014
F	ADDED SECOND ALTERNATE CONSTRUCTION BOTTOM VIEW. REQ. BY K. MUSTAFA.	21 JUL 2015

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ON Semiconductor and the are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative